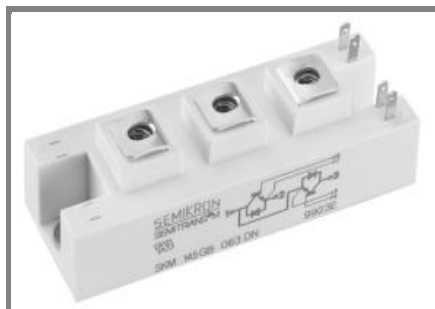


SKM 75GB176DN



SEMITRANS™ 2N

Trench IGBT Modules

SKM 75GB176DN

Preliminary Data

Features

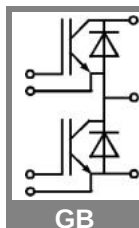
- Homogeneous Si
- Trench = Trench gate technology
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$

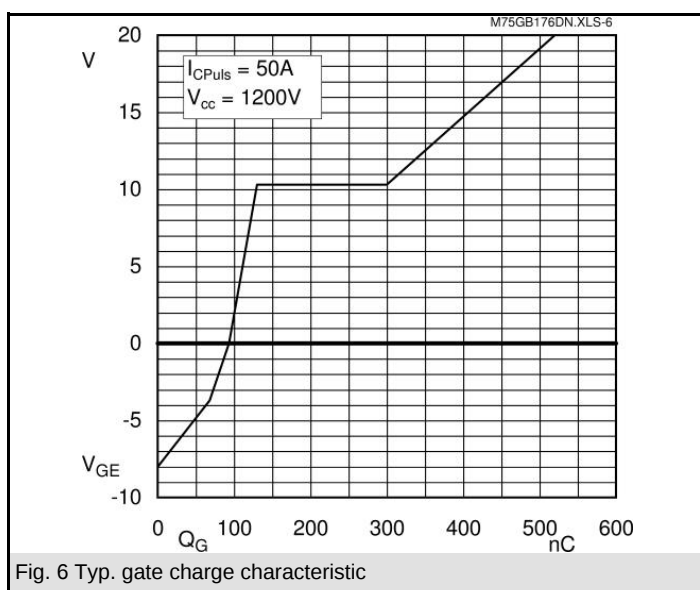
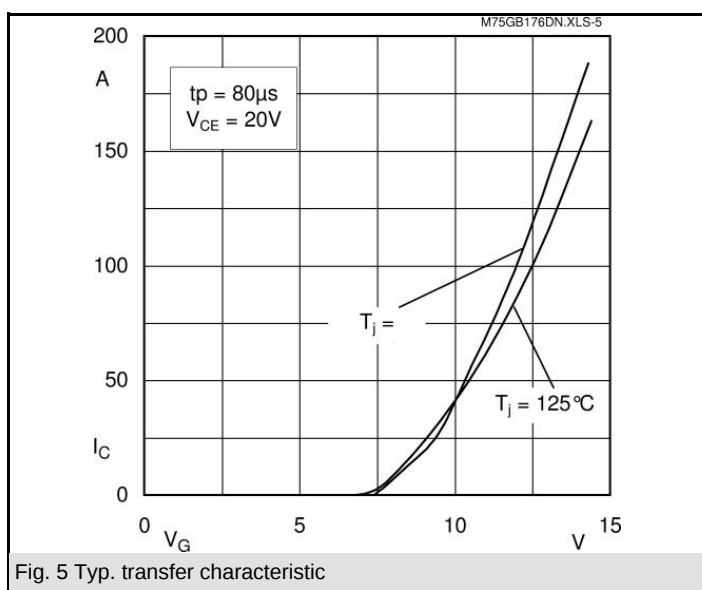
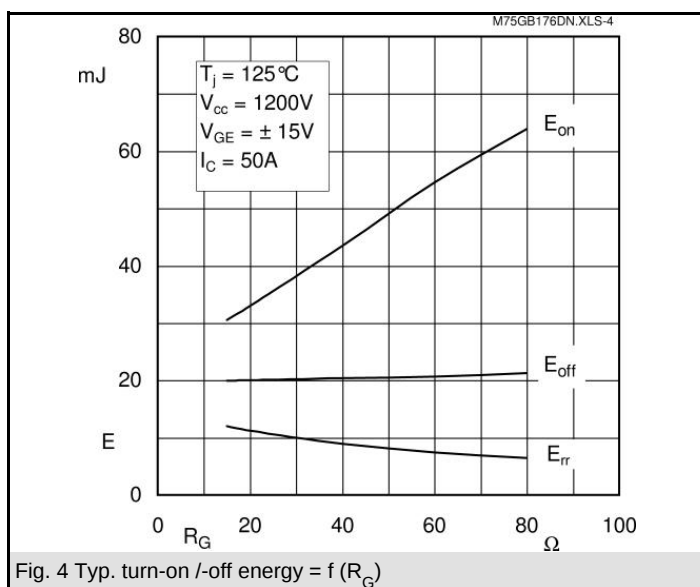
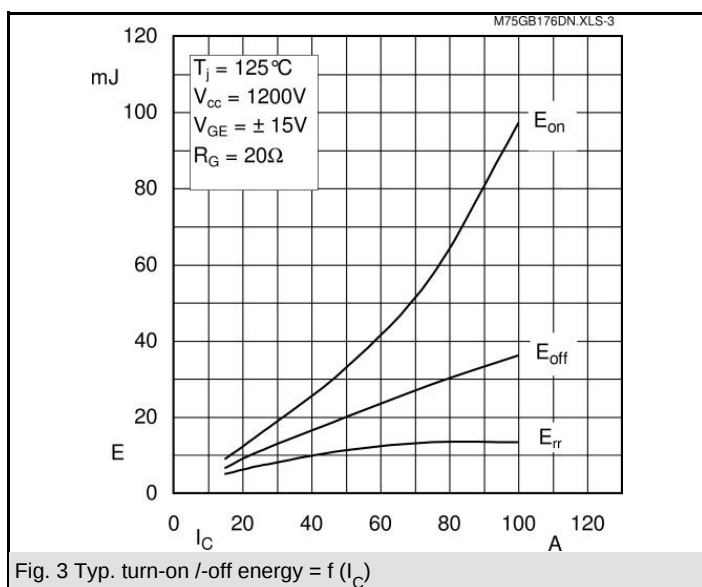
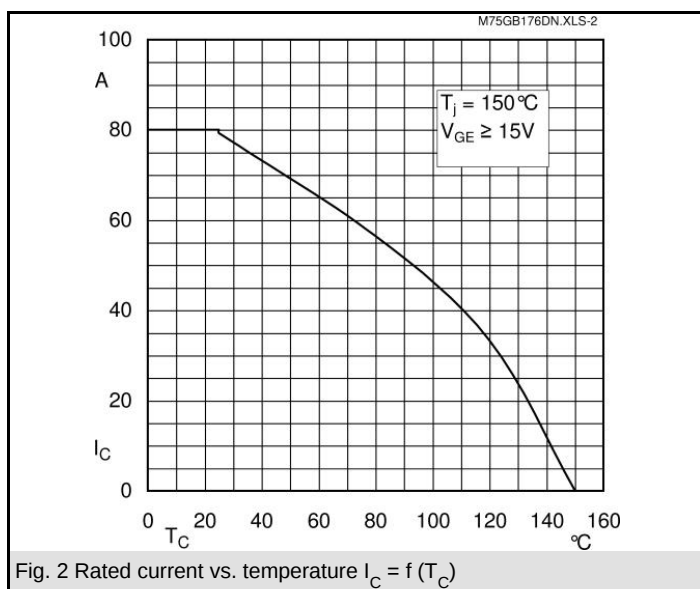
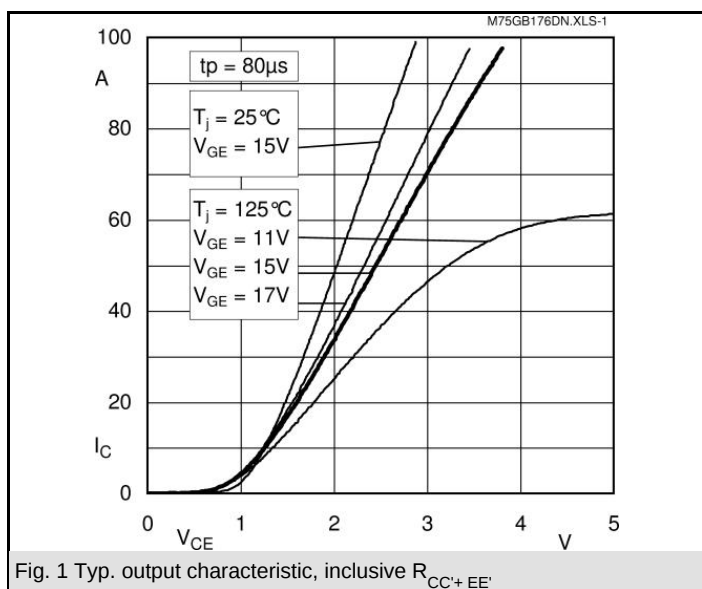
Typical Applications

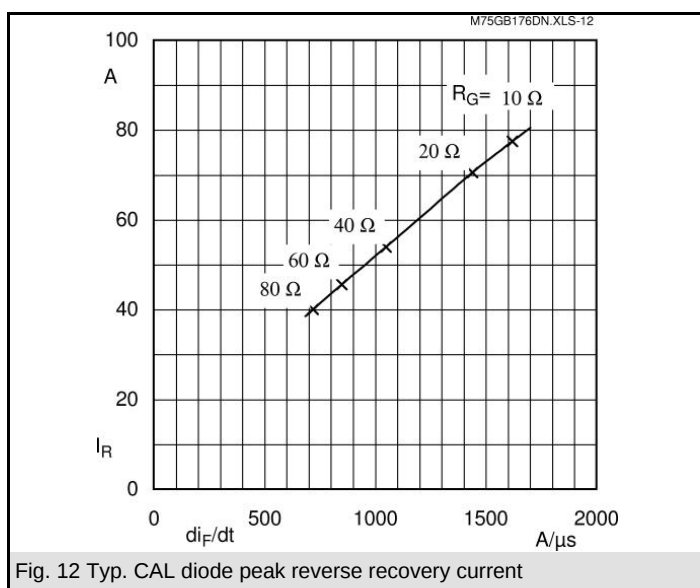
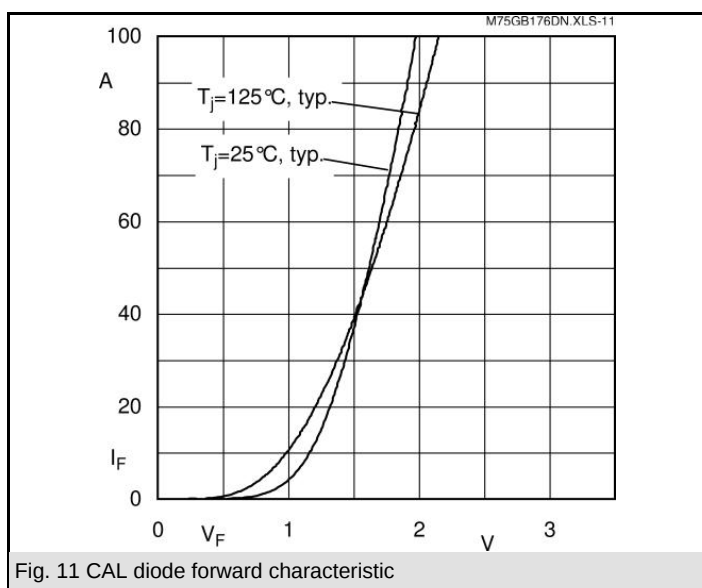
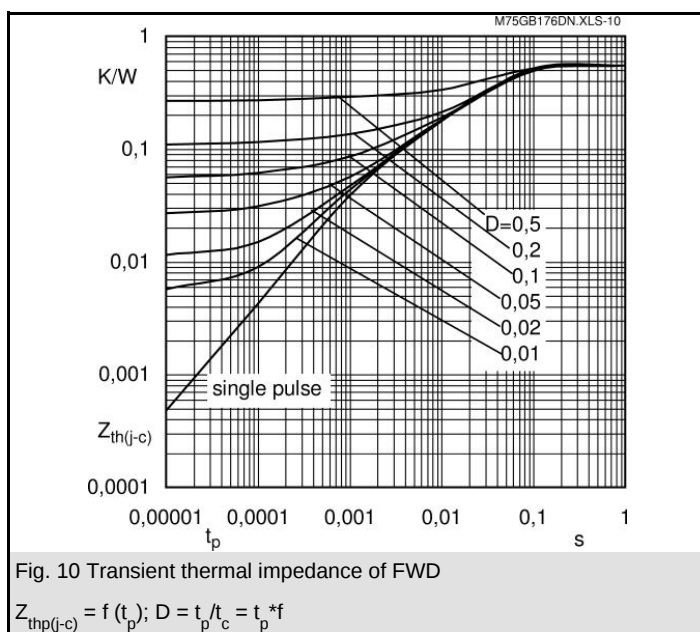
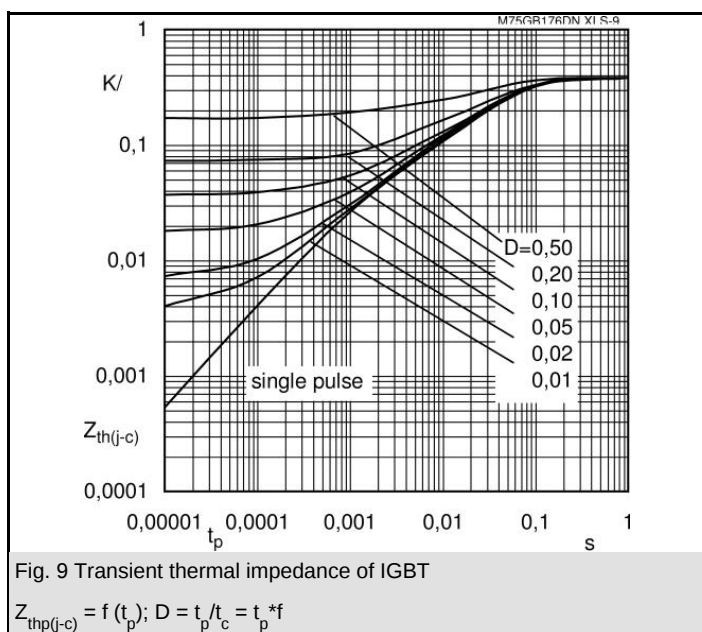
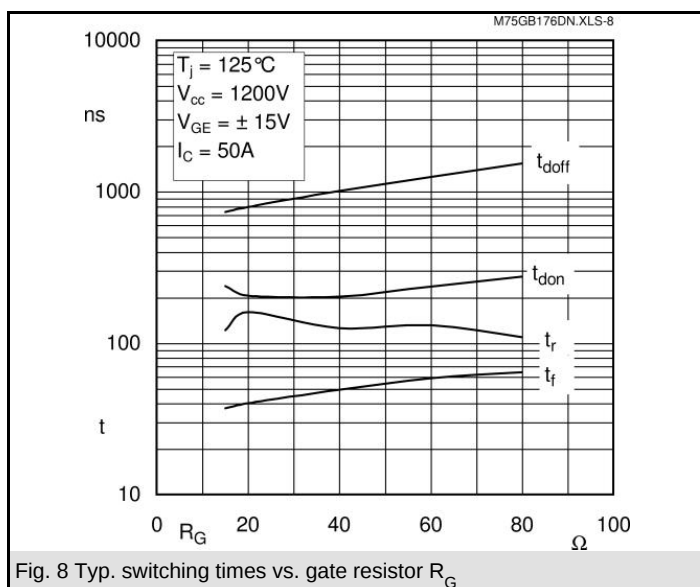
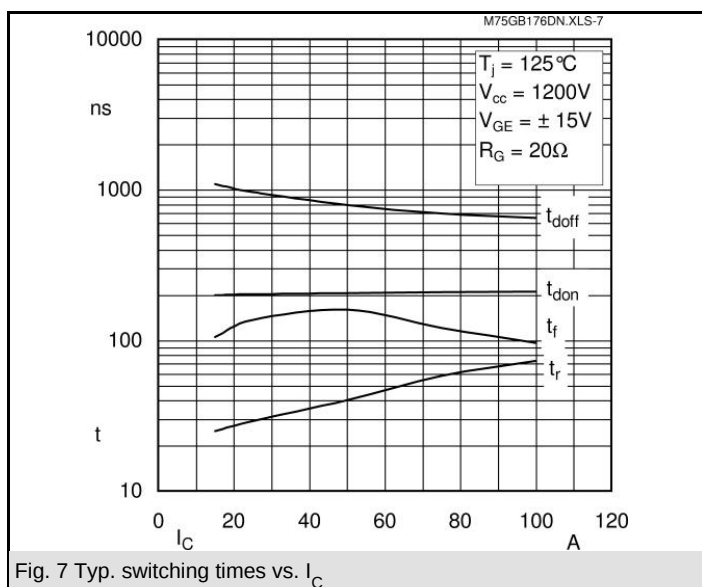
- AC inverter drives mains 575 - 750 V AC
- Public transport (auxiliary syst.)

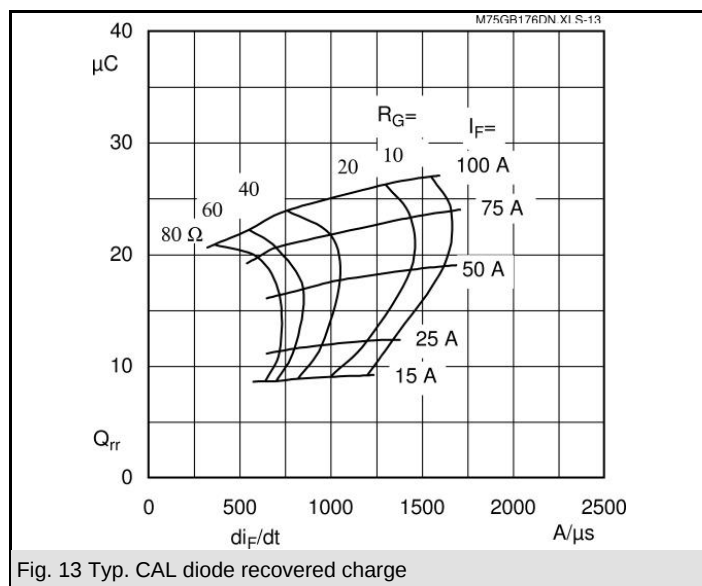
Absolute Maximum Ratings		$T_c = 25^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}		1700	V
I_C	$T_c = 25 (80)^\circ\text{C}$	80 (55)	A
I_{CRM}	$t_p = 1 \text{ ms}$	100	A
V_{GES}		± 20	V
T_{vj} (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)	$^\circ\text{C}$
V_{isol}	AC, 1 min.	4000	V
Inverse diode			
I_F	$T_c = 25 (80)^\circ\text{C}$	80 (55)	A
I_{FRM}	$t_p = 1 \text{ ms}$	100	A
I_{FSM}	$t_p = 10 \text{ ms}$; sin.; $T_j = 150^\circ\text{C}$	550	A

Characteristics		$T_c = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 2 \text{ mA}$	5,2	5,8	6,4	V
I_{CES}	$V_{GE} = 0$, $V_{CE} = V_{CES}$, $T_j = 25 ()^\circ\text{C}$		0,1	0,3	mA
$V_{CE(TO)}$	$T_j = 25 ()^\circ\text{C}$		1 (0,9)	1,2 (1,1)	V
r_{CE}	$V_{GE} = 15 \text{ V}$, $T_j = 25 (125)^\circ\text{C}$		20 (31)	25 (36)	m Ω
$V_{CE(sat)}$	$I_C = 50 \text{ A}$, $V_{GE} = 15 \text{ V}$, chip level		2 (2,45)	2,45 (2,9)	V
C_{ies}	under following conditions		4		nF
C_{oes}	$V_{GE} = 0$, $V_{CE} = 25 \text{ V}$, $f = 1 \text{ MHz}$		0,4		nF
C_{res}			0,3		nF
L_{CE}				25	nH
$R_{CC'+EE'}$	res., terminal-chip $T_c = 25 (125)^\circ\text{C}$		0,75 (1)		m Ω
$t_{d(on)}$	$V_{CC} = 1200 \text{ V}$, $I_C = 50 \text{ A}$		200		ns
t_r	$R_{Gon} = R_{Goff} = 20 \Omega$, $T_j = 125^\circ\text{C}$		40		ns
$t_{d(off)}$	$V_{GE} = \pm 15 \text{ V}$		790		ns
t_f			160		ns
$E_{on} (E_{off})$			33 (20)		mJ
Inverse diode					
$V_F = V_{EC}$	$I_F = 50 \text{ A}$; $V_{GE} = 0 \text{ V}$; $T_j = 25 (125)^\circ\text{C}$		1,7 (1,8)	1,9 (2)	V
$V_{(TO)}$	$T_j = 25 (125)^\circ\text{C}$		1,1 (0,9)	1,3 (1,1)	V
r_T	$T_j = 25 (125)^\circ\text{C}$		12 (18)	12 (18)	m Ω
I_{RRM}	$I_F = 50 \text{ A}$; $T_j = 25 (125)^\circ\text{C}$		(71)		A
Q_{rr}	$di/dt = 1440 \text{ A}/\mu\text{s}$		(18,6)		μC
E_{rr}	$V_{GE} = 0 \text{ V}$		(11,2)		mJ
Thermal characteristics					
$R_{th(j-c)}$	per IGBT			0,38	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,55	K/W
$R_{th(c-s)}$	per module			0,05	K/W
Mechanical data					
M_s	to heatsink M6	3		5	Nm
M_t	to terminals M5	2,5		5	Nm
w				160	g



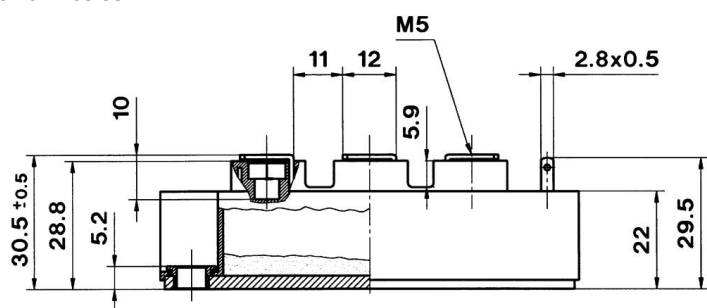




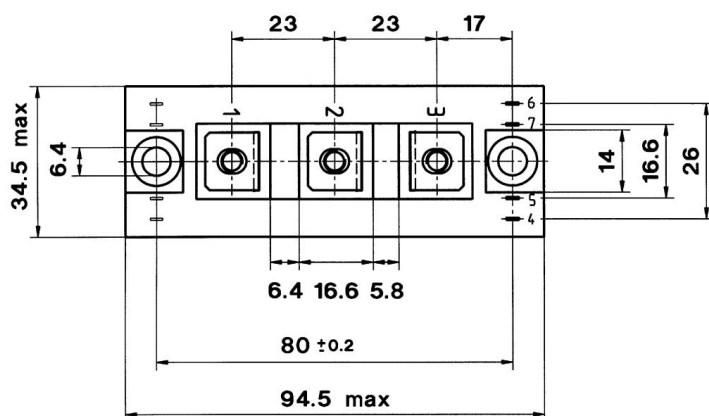


UL Recognized
File no. E 63 532

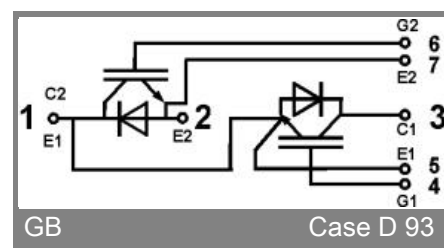
Dimensions in mm



CASED93



Case D 93



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.